

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series CT" triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ °C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- High immunity to false turn-on by dV/dt
- High voltage capability
- Isolated mounting base package
- Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Applications subject to high temperature ($T_{j(max)} = 150\text{ °C}$)
- Electronic thermostats
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids
- Refrigeration and air conditioning compressor

4. Quick reference data

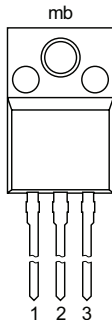
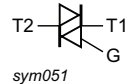
Table 1. Quick reference data

| Symbol | Parameter | Conditions | Values | Unit |
|--------------------------------|--------------------------------------|--|--------|------|
| Absolute maximum rating | | | | |
| V_{DRM} | repetitive peak off-state voltage | | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_h \leq 67\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | 16 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $t_p = 20\text{ ms}$; $T_{j(init)} = 25\text{ °C}$; Fig. 4 ; Fig. 5 | 140 | A |
| | | full sine wave; $t_p = 16.7\text{ ms}$; $T_{j(init)} = 25\text{ °C}$ | 150 | A |
| T_j | junction temperature | | 150 | °C |

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+$ $T_j = 25\text{ °C};$ Fig. 7 | 2 | - | 35 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-$ $T_j = 25\text{ °C};$ Fig. 7 | 2 | - | 35 | mA |
| | | $V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-$ $T_j = 25\text{ °C};$ Fig. 7 | 2 | - | 35 | mA |
| I_H | holding current | $V_D = 12\text{ V}; T_j = 25\text{ °C};$ Fig. 9 | - | - | 35 | mA |
| V_T | on-state voltage | $I_T = 18\text{ A}; T_j = 25\text{ °C};$ Fig. 10 | - | 1.3 | 1.5 | V |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}; T_j = 125\text{ °C}; (V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 500 | - | - | V/ μ s |
| | | $V_{DM} = 536\text{ V}; T_j = 150\text{ °C}; (V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 200 | - | - | V/ μ s |
| dI_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}; T_j = 150\text{ °C}; I_{T(RMS)} = 16\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ gate open circuit; snubberless condition | 8 | - | - | A/ms |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--|---|
| 1 | T1 | main terminal 1 |  |  |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|---------------|---------|---|---------|
| | Name | Description | Version |
| BTA316X-800CT | TO-220F | Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack' | SOT186A |

7. Marking

Table 4. Marking codes

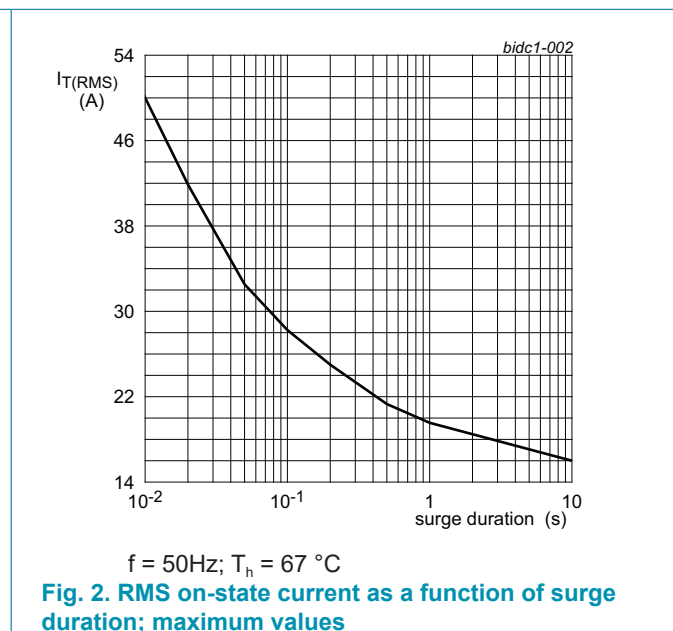
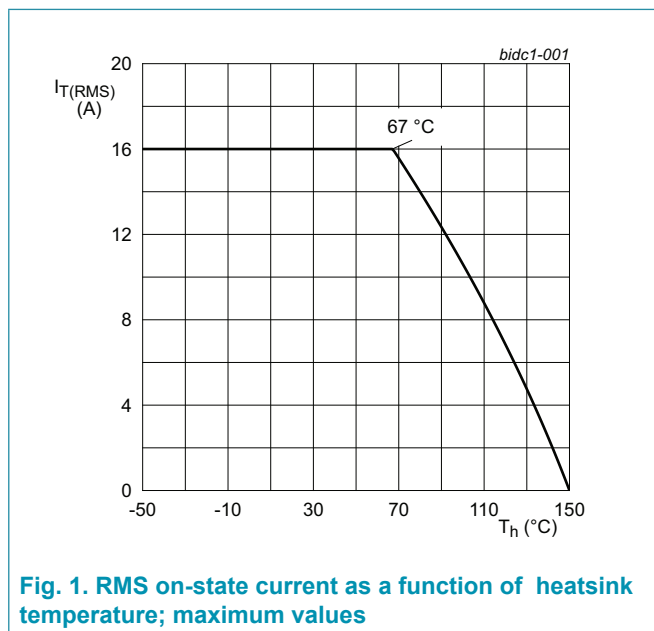
| Type number | Marking codes |
|---------------|---------------|
| BTA316X-800CT | BTA316X-800CT |

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Values | Unit |
|--------------|--------------------------------------|---|------------|------------------------|
| V_{DRM} | repetitive peak off-state voltage | | 800 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_h \leq 67\text{ }^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | 16 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $t_p = 20\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; Fig. 4 ; Fig. 5 | 140 | A |
| | | full sine wave; $t_p = 16.7\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ | 150 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ms}$; sine wave | 98 | A^2s |
| dI_T/dt | rate of rise of on-state current | $I_G = 70\text{mA}$ | 100 | $\text{A}/\mu\text{s}$ |
| I_{GM} | peak gate current | | 2 | A |
| P_{GM} | peak gate power | | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | 0.5 | W |
| T_{stg} | storage temperature | | -40 to 150 | $^\circ\text{C}$ |
| T_j | junction temperature | | 150 | $^\circ\text{C}$ |



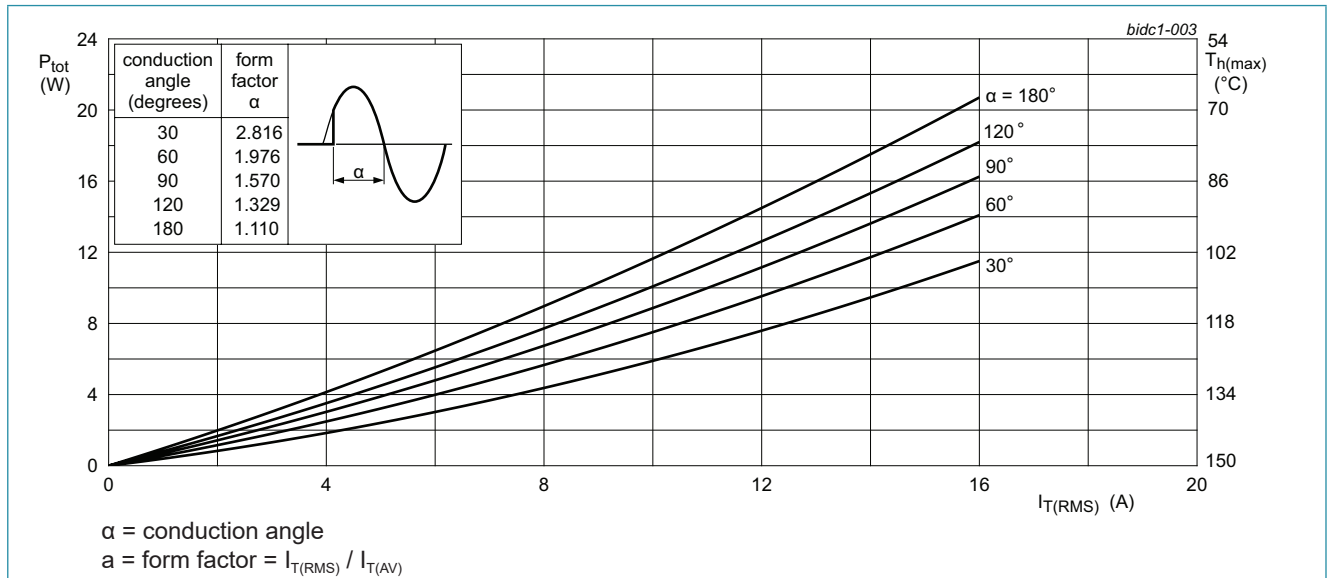


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

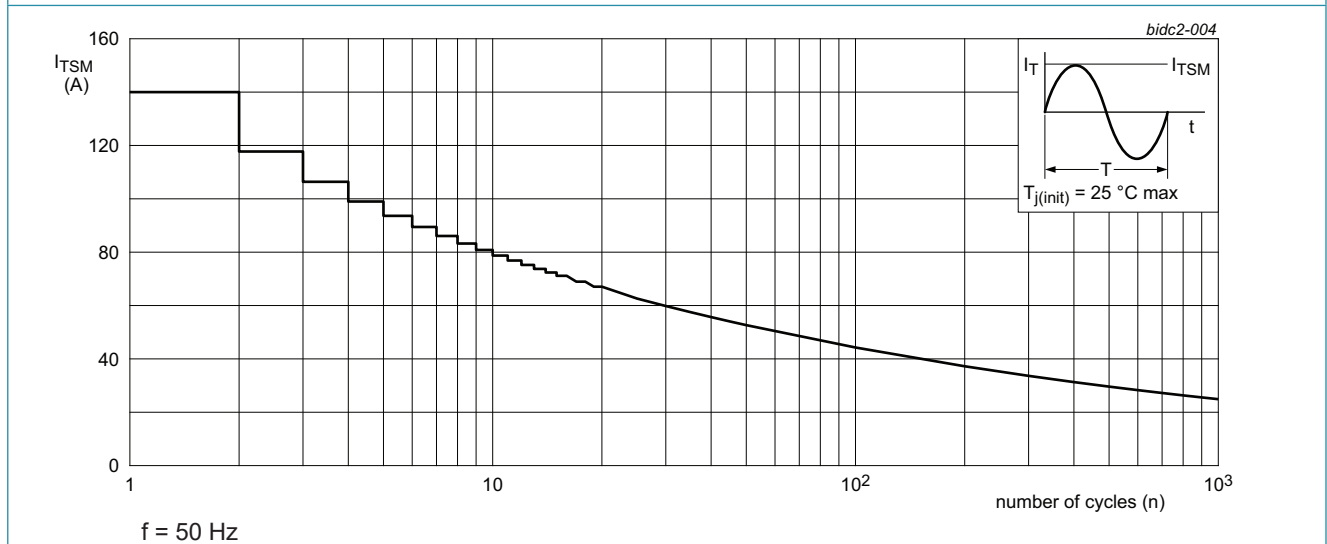


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

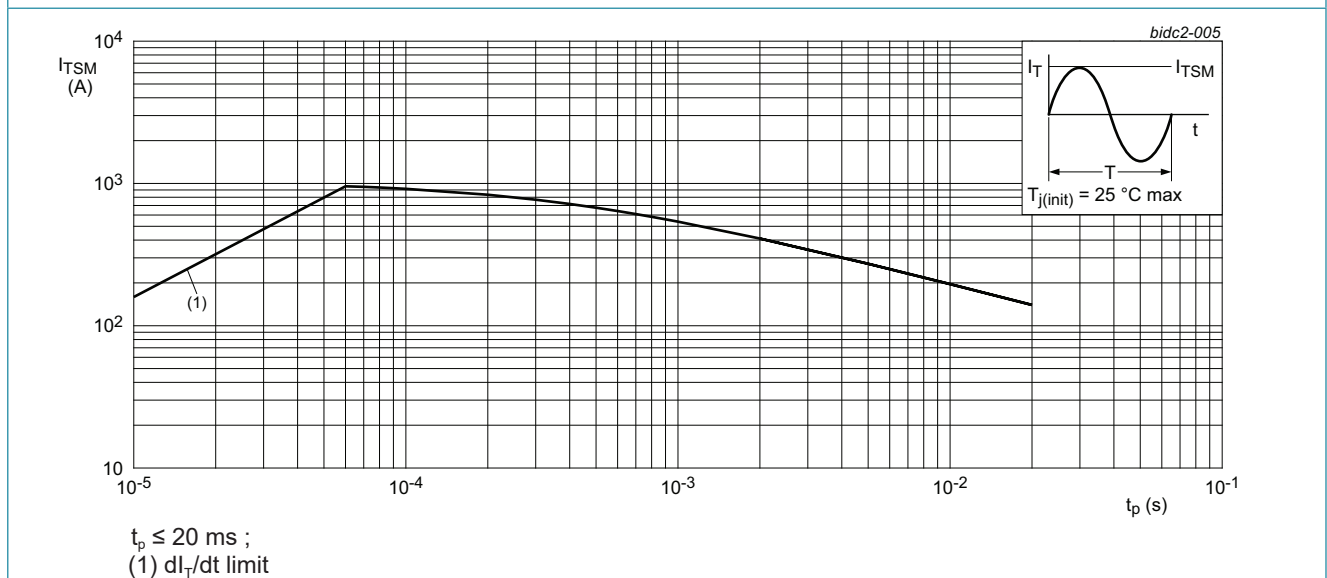


Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

9. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|--|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | with heatsink compound; Fig. 6 | - | - | 4 | K/W |
| | | without heatsinkcompound; Fig. 6 | - | - | 5.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 55 | - | K/W |

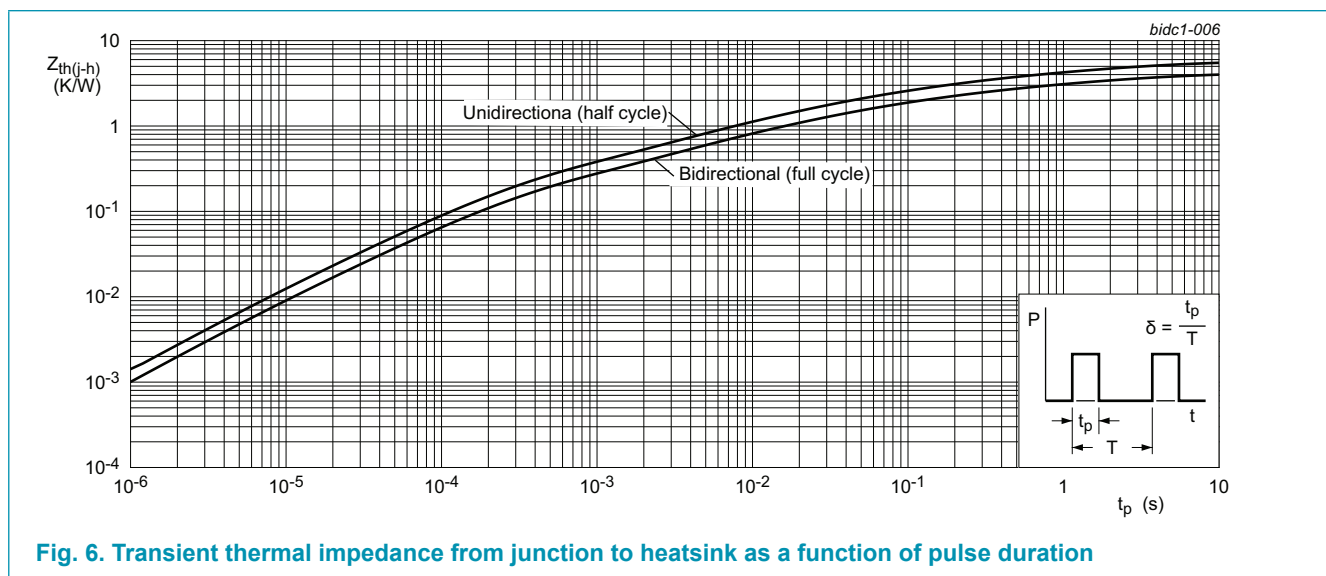


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

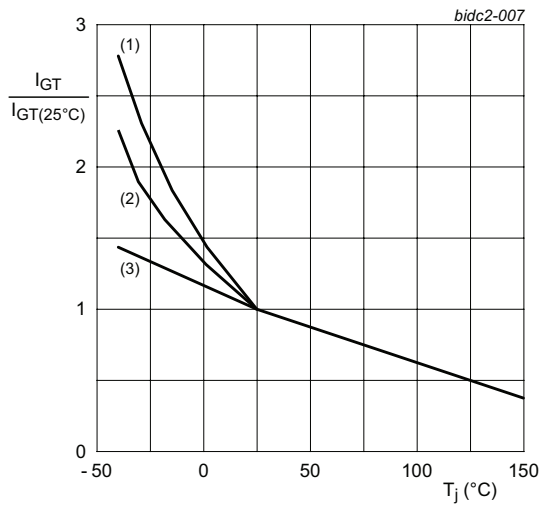
Table 6. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|---|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C_{isol} | isolation capacitance | from cathode to external heatsink | - | 10 | - | PF |

11. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|---|------|-----|-----|------------------|
| Static characteristics | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 7 | 2 | - | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 7 | 2 | - | 35 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 7 | 2 | - | 35 | mA |
| I_L | latching current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 8 | - | - | 50 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 8 | - | - | 60 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 8 | - | - | 50 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 9 | - | - | 35 | mA |
| V_T | on-state voltage | $I_T = 18\text{ A}$; $T_J = 25\text{ °C}$; Fig. 10 | - | 1.3 | 1.5 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$; Fig. 11 | - | 0.8 | 1 | V |
| | | $V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 150\text{ °C}$; Fig. 11 | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = 800\text{ V}$; $T_J = 25\text{ °C}$ | - | - | 10 | μA |
| | | $V_D = 800\text{ V}$; $T_J = 150\text{ °C}$ | - | - | 2 | mA |
| Dynamic characteristics | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 536\text{ V}$; $T_J = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 500 | - | - | V/ μs |
| | | $V_{DM} = 536\text{ V}$; $T_J = 150\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | 200 | - | - | V/ μs |
| dI_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}$; $T_J = 150\text{ °C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit; snubberless condition | 8 | - | - | A/ms |



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

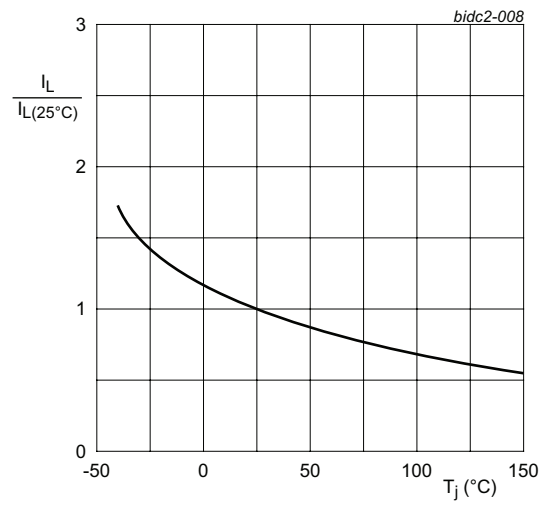


Fig. 8. Normalized latching current as a function of junction temperature

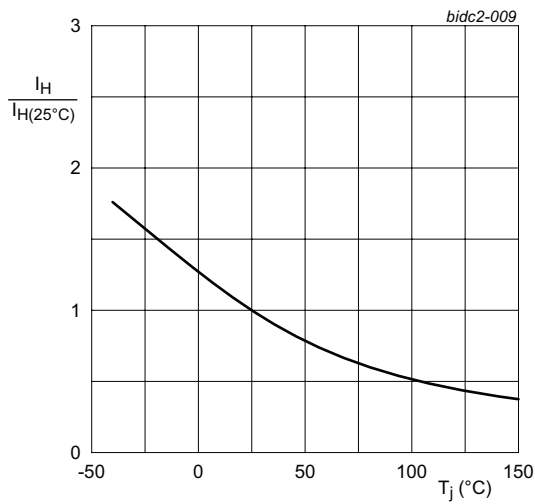
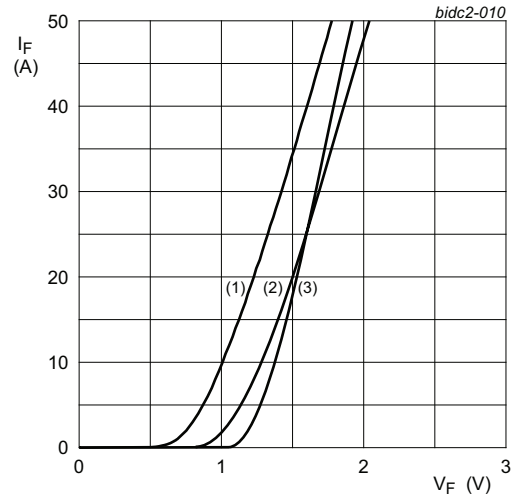


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.053 \text{ V}$; $R_s = 0.0216 \ \Omega$

- (1) $T_j = 150^\circ\text{C}$; typical values
- (2) $T_j = 150^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

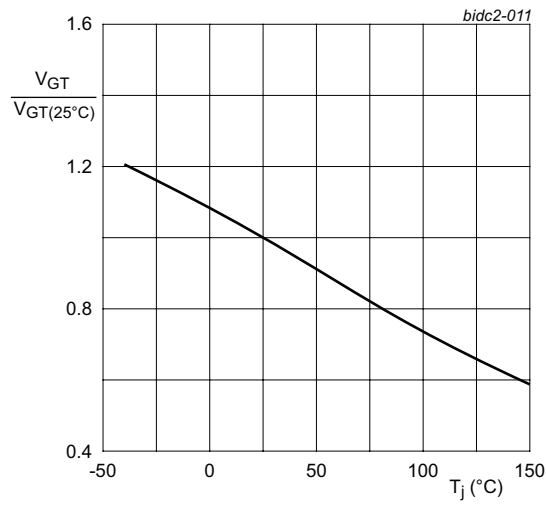
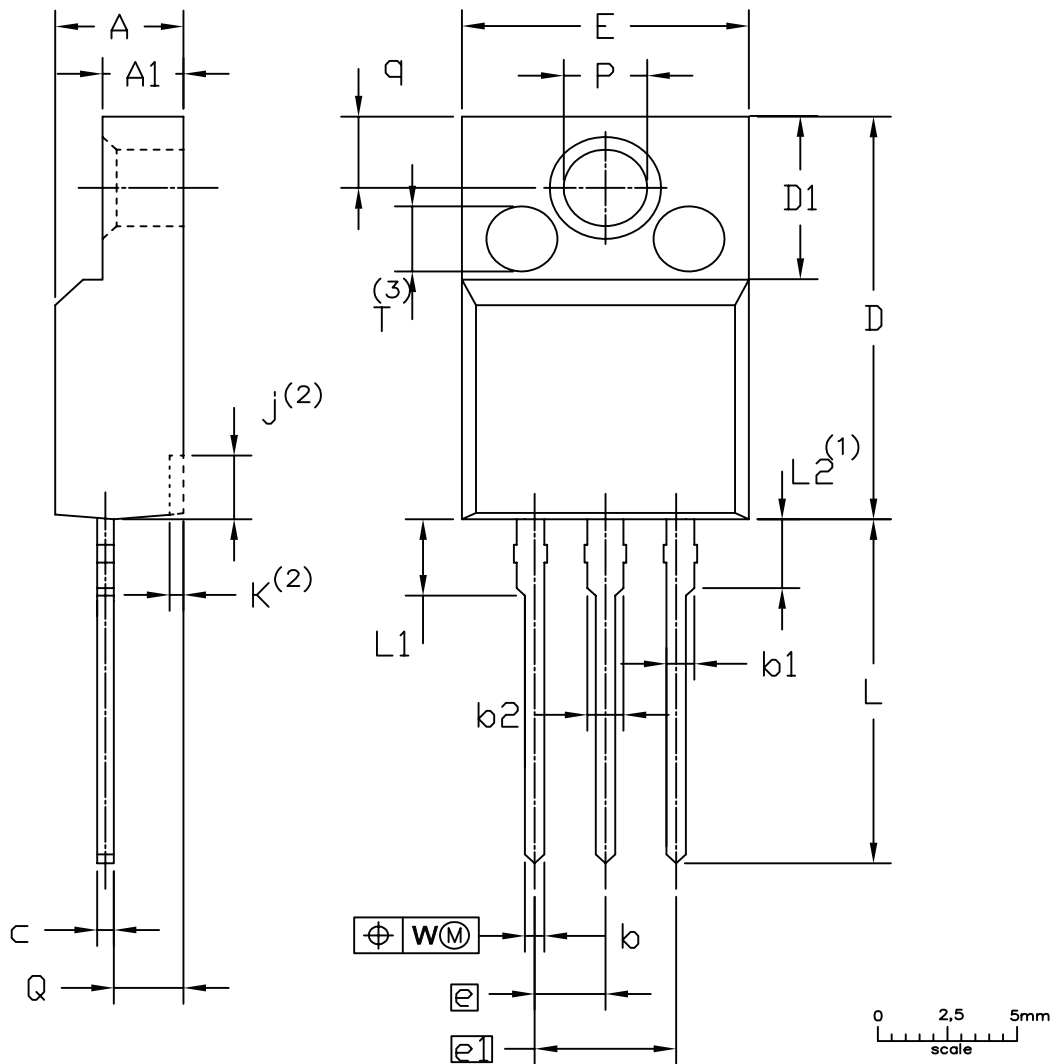


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"

SOT186A



| UNIT | A | A ₁ | b | b ₁ | b ₂ | c | D | D ₁ | E | e | e ₁ | j ⁽²⁾ | k ⁽²⁾ | L | L ₁ | L ₂ ⁽¹⁾ max. | P | Q | q | W | T ⁽³⁾ |
|------|-----|----------------|-----|----------------|----------------|-----|------|----------------|------|------|----------------|------------------|------------------|------|----------------|---------------------------------------|-----|-----|-----|-----|------------------|
| mm | 4.6 | 2.9 | 0.9 | 1.1 | 1.4 | 0.7 | 15.8 | 6.5 | 10.3 | 2.54 | 5.08 | 2.7 | 0.6 | 14.4 | 3.30 | 3 | 3.2 | 2.6 | 3.0 | 0.4 | 2.5 |
| | 4.0 | 2.5 | 0.7 | 0.9 | 1.0 | 0.4 | 15.2 | 6.3 | 9.7 | | | 1.7 | 0.4 | 13.5 | 2.79 | | 3.0 | 2.3 | 2.6 | | |

Notes

- Terminal dimensions within this zone are uncontrolled
- Dot lines area designs may vary
- Eject pin mark is for reference only

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|----------------|-------|------------------------|------------|
| | IEC | JEDEC | JEITA | | |
| SOT186A | | 3 LEADS TO220F | | | 2013-11-14 |

13. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 12 September 2018

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